WHAT IS CLAIMED IS:

1. A semiconductor device, comprising:

a substrate including an active pattern;

a gate electrode running across the active pattern;

a source/drain pattern adjacent to one side of the gate electrode and on an upper portion of the active pattern;

an active contact electrically connected to the source/drain pattern; and

a silicide layer between the source/drain pattern and the active contact,

wherein the source/drain pattern includes:

a body part including a plurality of semiconductor patterns; and

a capping pattern on the body part,

wherein:

the body part has a first facet, a second facet on the first facet, and a corner edge defined where the first facet meets the second facet, the corner edge extending parallel to the substrate,

the capping pattern covers the second facet of the body part and exposes the corner edge, and

the silicide layer covers a top surface of the body part and a top surface of the capping pattern,

the body part includes:

a first semiconductor pattern of the plurality of semiconductor patterns having a valley on a top surface of the first semiconductor pattern;

a second semiconductor pattern of the plurality of semiconductor patterns filling the valley; and

a third semiconductor pattern that is an outermost one of the plurality of semiconductor patterns,

the first semiconductor pattern and the second semiconductor pattern include silicon-germanium,

the third semiconductor pattern includes silicon, ~~and~~

a silicon content of the third semiconductor pattern is about 95 at% to about 100 at%, and

the source/drain pattern has a maximum width at a level at which the corner edge is located.

2. The semiconductor device as claimed in claim 1, wherein:

the capping pattern includes germanium, and

a germanium content of the capping pattern is about 5 at% to about 100 at%.

~~3. The semiconductor device as claimed in claim 1 or claim 2, wherein:~~

~~the capping pattern covers the second facet.~~

~~4. The semiconductor device as claimed in any one of claims 1 to 3, wherein the source/drain pattern has a maximum width at a level at which the corner edge is located.~~

~~5~~3. The semiconductor device as claimed in ~~any one of claims 1 to 4~~claim 1 or claim 2, wherein the capping pattern exposes the first facet.

~~6~~4. The semiconductor device as claimed in ~~any one of claims 1 to 4~~claim 1 or claim 2, wherein the capping pattern covers the first facet.

~~7~~5. The semiconductor device as claimed in any one of claims 1 to ~~6~~4, wherein:

the active pattern includes a plurality of active patterns that are adjacent to each other in an extending direction of the gate electrode,

the source/drain pattern is on the plurality of active patterns, and

the silicide layer covers the top surface of the first semiconductor pattern and a top surface of the second semiconductor pattern.

~~8~~6. The semiconductor device as claimed in any one of claims 1 to ~~7~~5, wherein:

the third semiconductor pattern is between the first semiconductor pattern and the capping pattern, and

the second semiconductor pattern is spaced apart from the capping pattern.

~~9~~7. The semiconductor device as claimed in any one of claims 1 to ~~8~~6, further comprising a device isolation layer that covers a lower sidewall of the active pattern on the substrate,

wherein the upper portion of the active pattern extends vertically beyond the device isolation layer.

~~10~~8. A semiconductor device, comprising:

a substrate including an active pattern;

a gate electrode running across the active pattern and extending in a first direction; and

a source/drain pattern adjacent to one side of the gate electrode and on an upper portion of the active pattern,

wherein the source/drain pattern includes:

a body part including a plurality of semiconductor patterns; and

a capping pattern on the body part,

wherein the body part has a first semiconductor pattern that is an outermost one of the plurality of semiconductor patterns, the first semiconductor pattern including silicon in an amount of about 95 at% to about 100 at%,

wherein the capping pattern includes germanium, a germanium content of the capping pattern being about 5 at% to about 100 at%,

wherein the capping pattern covers one facet of the first semiconductor pattern and exposes a corner edge of the body part, and

wherein the source/drain pattern has a maximum width in the first direction at a level at which the corner edge is located.

~~11~~9. The semiconductor device as claimed in claim ~~10~~8, further comprising:

an active contact electrically connected to the source/drain pattern; and

a silicide layer between the source/drain pattern and the active contact,

wherein the silicide layer covers a top surface of the body part and a top surface of the capping pattern.

~~12~~10. The semiconductor device as claimed in claim ~~10~~ 8 or claim ~~11~~9, wherein the one facet of the first semiconductor pattern is a (111) plane.

~~13~~11. The semiconductor device as claimed in any one of claims ~~10~~ 8 to ~~12~~10, wherein:

the body part includes a second semiconductor pattern between the first semiconductor pattern and the active pattern, and

the second semiconductor pattern includes silicon-germanium.

~~14~~12. The semiconductor device as claimed in claim ~~13~~11, wherein the germanium content of the capping pattern is greater than a germanium content of the second semiconductor pattern.

~~15~~13. A semiconductor device, comprising:

a substrate including an active pattern;

a gate electrode running across the active pattern and extending in a first direction; and

a source/drain pattern adjacent to one side of the gate electrode and on an upper portion of the active pattern,

wherein the source/drain pattern includes:

a body part including a plurality of semiconductor patterns; and

a capping pattern on the body part,

wherein the body part includes a corner edge that horizontally protrudes in the first direction,

wherein the capping pattern exposes the corner edge of the body part,

wherein a germanium content of the capping pattern is greater than a germanium content of the body part, and

wherein the source/drain pattern has a maximum width in the first direction at a level at which the corner edge is located.

~~16~~14. The semiconductor device as claimed in claim ~~15~~13, wherein:

the corner edge is defined by a first facet and a second facet of the body part, and

each of the first facet and the second facet is a (111) plane.

~~17~~15. The semiconductor device as claimed in claim ~~16~~14, wherein the capping pattern covers one or more of the first facet and the second facet.

~~18~~16. The semiconductor device as claimed in any one of claims ~~15~~ 13 to ~~17~~15, further comprising:

an active contact electrically connected to the source/drain pattern; and

a silicide layer between the source/drain pattern and the active contact,

wherein the silicide layer covers a top surface of the body part and a top surface of the capping pattern.